



PRODUCT DATA



Micro International, Inc

PART NUMBER

LDT2484 and LDT2484T

Micro-LID NPN Transistor



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**Micro-LID Transistors
LDT2484 and LDT2484T**

Description:

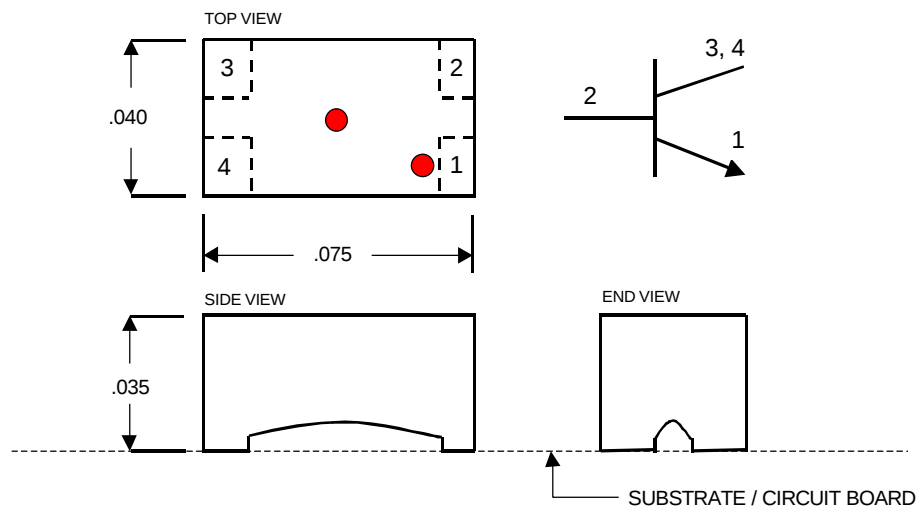
The LDT2484 (untinned) and LDT2484T (tinned) are NPN silicon transistors in very small, rugged, surface mount, 4-post ceramic packages (Micro International manufactured package p/n 4-075-1). The LDT2484 and LDT2484T meet the general specifications of the 2N2484 transistor. The 4-075-1 Micro-LID package is a 4-post, leadless ceramic carrier which can be provided with gold metallized or pre-tinned lands, and is approved for military, medical implant, sensor, and high reliability applications. The LDT2484 and LDT2484T can be provided with special feature options such as additional temperature cycling and screening.

Maximum Ratings:

Parameter	Symbol	Rating
Collector-Base Voltage	Vcbo	60 V
Collector-Emitter Voltage	Vceo	60 V
Emitter-Base Voltage	Vebo	6 V
Collector Current	Ic	50 mA
Total Dissipation	Pt	350 mW
Operating Junction Temperature	Tj	150°C
Storage Temperature	Tstg	-65°C to 150°C
Operating Temperature	Toper	-55°C to 125°C

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Outline / Schematic:



Dimensions / Marking:

Length	.075" $\pm$.003"	Post 1 (Emitter)	.015" x .010" typ
Width	.040" $\pm$.003"	Post 2 (Base)	.015" x .010" typ
Height	.035" $\pm$.003"	Post 3,4 (Collector)	.015" x .012" typ

Marking on back of package: Red Dot over Emitter and Red Dot in Center
(post down configuration)

Standard In-Process Screening Requirements:

- Semiconductor die and Micro-LID package visual inspection
- Wire pull test
- 24 hour stabilization bake at 150°C
- 10 temperature cycles from -55°C to 125°C
- 100% electrical test of dc characteristics at 25°C
- Final visual inspection

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Electrical Characteristics (25 °C Ambient)

Parameter	Symbol	Min	Typ	Max	Units
Collector-Base Breakdown $I_c = 10 \mu A, I_e = 0$	BVcbo	60	--	--	V
Collector-Emitter Breakdown* $I_b = 0, I_c = 10 \text{ mA}$	BVceo	60	--	--	V
Emitter-Base Breakdown $I_c = 0, I_e = 10 \mu A$	BVebo	6	--	--	V
Collector-Base Cutoff Current $V_{cb} = 45 \text{ V}$	Icbo	--	--	10	nA
Emitter-Base Cutoff Current $V_{eb} = 5 \text{ V}$	Iebo	--	--	10	nA
DC Forward Current Gain* $I_c = 10 \mu A, V_{ce} = 5 \text{ V}$ $I_c = 1 \text{ mA}, V_{ce} = 5 \text{ V}$	Hfe	100 200	-- --	500 800	
Collector-Emitter Saturation $I_c = 1 \text{ mA}, I_b = 100 \mu A$	Vce (sat)	--	--	.35	V
Base-Emitter Saturation $I_c = 1 \text{ mA}, I_b = 100 \mu A$	Vbe (sat)	--	--	1	V
Collector Capacitance $V_{cb} = 10 \text{ V}, I_e = 0$ $f = 1 \text{ MHz}$	Cobo	--	--	5	pF

* Pulse test, pulse width $\leq 300 \mu\text{sec}$, duty cycle $\leq 2\%$